

## SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

# MCH3375 — General-Purpose Switching Device Applications

#### **Features**

- ON-resistance RDS(on)1=227m $\Omega$ (typ.)
- · 4V drive
- · Halogen free compliance

#### **Specifications**

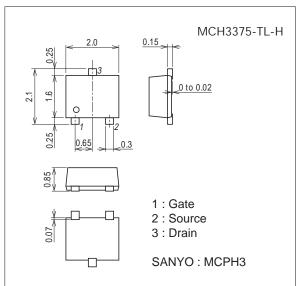
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-1.6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-6.4	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> x0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

#### **Package Dimensions**

unit : mm (typ) 7019A-003

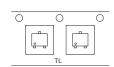


#### **Product & Package Information**

• Package : MCPH3

JEITA, JEDEC : SC-70, SOT-323
 Minimum Packing Quantity : 3,000 pcs./reel

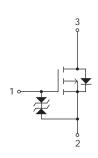
#### Packing Type: TL



### Marking



#### **Electrical Connection**



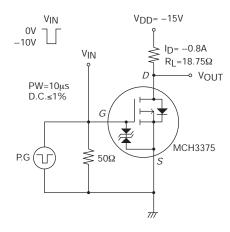
<sup>\*</sup> Machine Model

#### MCH3375

#### Electrical Characteristics at Ta=25°C

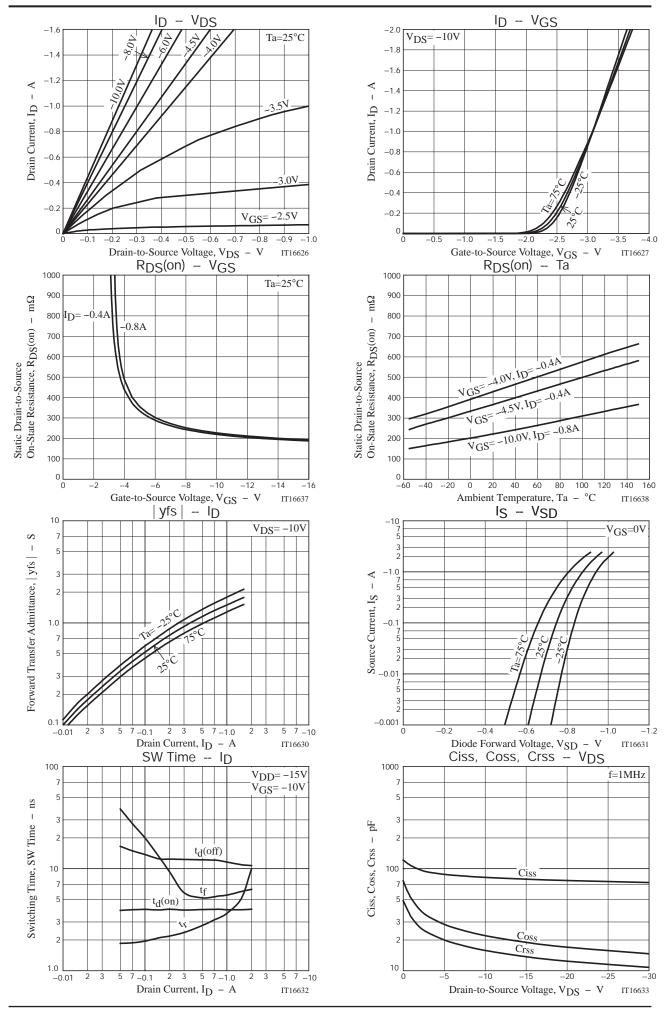
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V	
Forward Transfer Admittance	yfs	VDS=-10V, ID=-0.8A		1.3		S	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =-0.8A, V <sub>G</sub> S=-10V		227	295	mΩ	
	R <sub>DS</sub> (on)2	I <sub>D</sub> =-0.4A, V <sub>G</sub> S=-4.5V		374	523	mΩ	
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.4A, V <sub>G</sub> S=-4V		435	609	mΩ	
Input Capacitance	Ciss			82		pF	
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		22		pF	
Reverse Transfer Capacitance	Crss			16		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			4.0		ns	
Rise Time	t <sub>r</sub>	Considered Total Circuit		3.3		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		12		ns	
Fall Time	tf			5.4		ns	
Total Gate Charge	Qg			2.2		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.6A		0.36		nC	
Gate-to-Drain "Miller" Charge	Qgd			0.49		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.6A, V <sub>GS</sub> =0V		-0.9	-1.5	V	

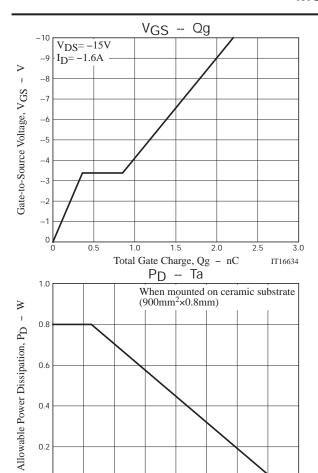
#### Switching Time Test Circuit



#### **Ordering Information**

Device	Package	Shipping	memo	
MCH3375-TL-H	МСРН3	3,000pcs./reel	Pb Free and Halogen Free	





0 L

20

60

80

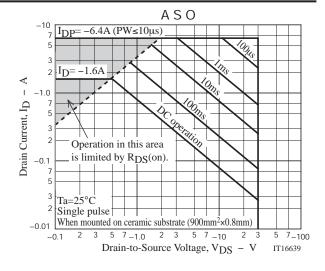
Ambient Temperature, Ta - °C

100

140

<u>1</u>60

IT16640

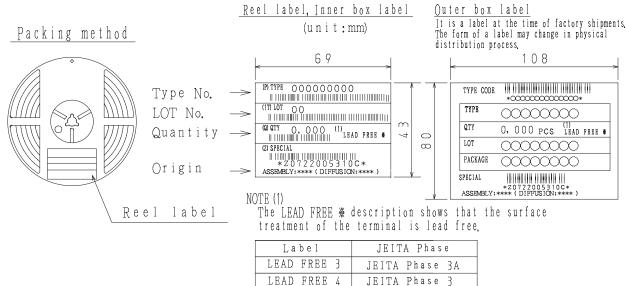


#### **Taping Specification**

#### MCH3375-TL-H

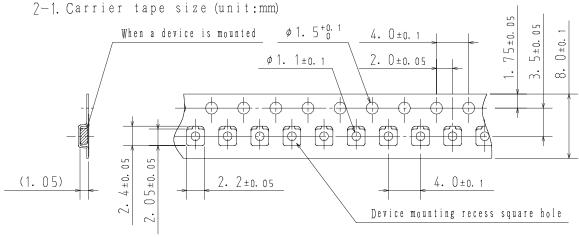
#### 1. Packing Format

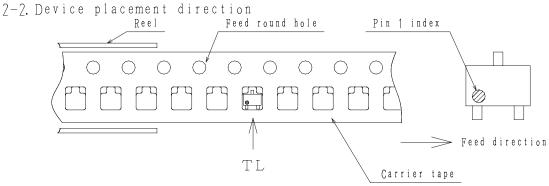
Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
мсрн3	мсрн3	3,000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



JEITA Phase 3

#### 7. Taping configuration

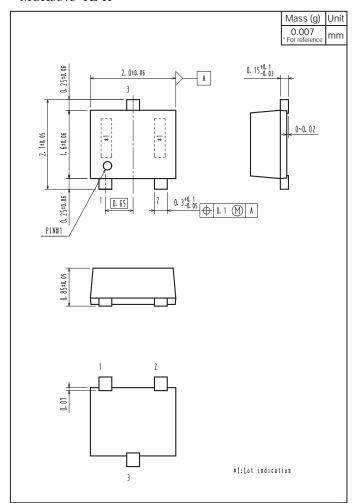




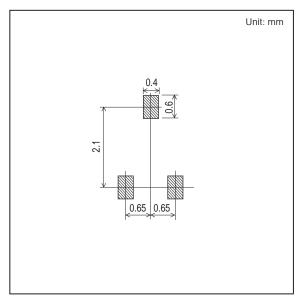
Those with pin 1 index on the feed hole side·····TL

## **Outline Drawing**

## MCH3375-TL-H



#### Land Pattern Example



Note on usage: Since the MCH3375 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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